



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23-3L Plastic-Encapsulate Transistors

2SC2734 TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 0.15 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 0.05 A

Collector-base voltage

$V_{(BR)CBO}$: 20 V

Operating and storage junction temperature range

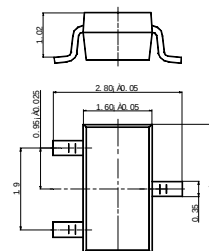
T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-23-3L

1. BASE

2. EMITTER

3. COLLECTOR



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	20		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	11		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	3		V
Collector cut-off current	I_{CBO}	$V_{CB}=10V, I_E=0$		0.5	μA
DC current gain	h_{FE}	$V_{CE}=10V, I_C=5mA$	20	200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=10mA, I_B=5mA$		0.7	V
Transition frequency	f_T	$V_{CE}=10V, I_C=10mA$	1.4		GHz
Collector output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$		1.5	pF
Noise figure	NF	$V_{CC}=6V, I_C=2mA, f_{out}=30MHz$ $f=900MHz, f_{osc}=930MHz$		12	dB

Marking

GC